



ON Semiconductor®

BC517 NPN Darlington Transistor

Features

- This device is designed for applications requiring extremely high current gain at currents to 1.0 A.
- Sourced from process 05.



Ordering Information

Part Number	Top Mark	Package	Packing Method
BC517-D74Z	BC517	TO-92 3L (Bent Lead)	Ammo

Absolute Maximum Ratings^{(1), (2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current - Continuous	1.2	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Notes:

1. These ratings are based on a maximum junction temperature of 150°C .
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics⁽³⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Total Device Dissipation, $T_A = 25^\circ\text{C}$	625	mW
	Derate Above 25°C	5.0	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	83.3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ\text{C/W}$

Note:

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 2.0\text{ mA}, I_B = 0$	30			V
V_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	40			V
V_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\ \text{nA}, I_C = 0$	10			V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 30\ \text{V}, I_E = 0$			100	nA
h_{FE}	DC Current Gain	$V_{CE} = 2\ \text{V}, I_C = 20\ \text{mA}$	30,000			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\ \text{mA}, I_B = 0.1\ \text{mA}$			1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 10\ \text{mA}, V_{CE} = 5.0\ \text{V}$			1.4	V

Typical Performance Characteristics

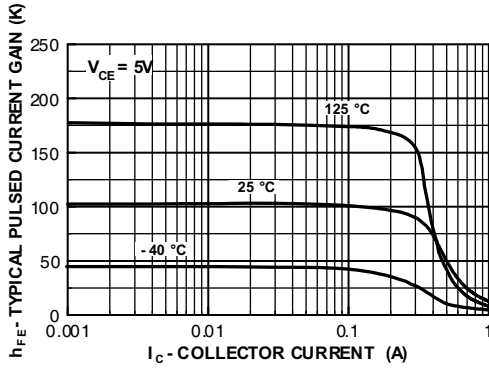


Figure 1. Typical Pulsed Current Gain vs. Collector Current

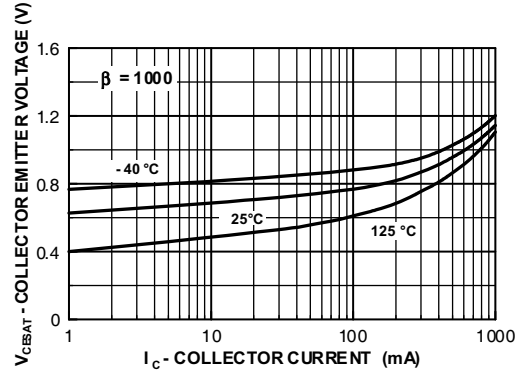


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

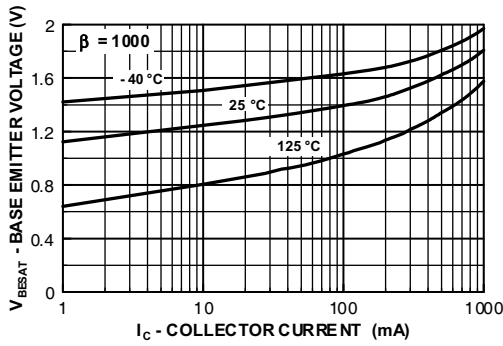


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

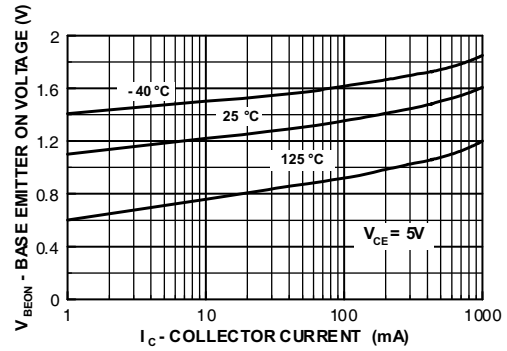


Figure 4. Base Emitter On Voltage vs. Collector Current

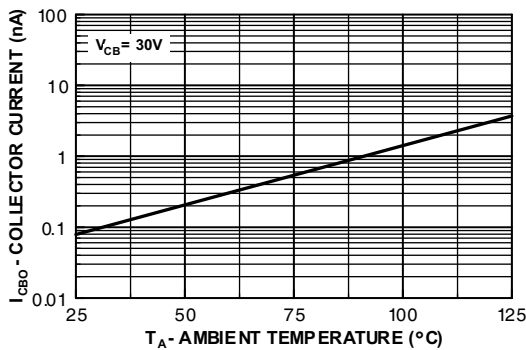


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

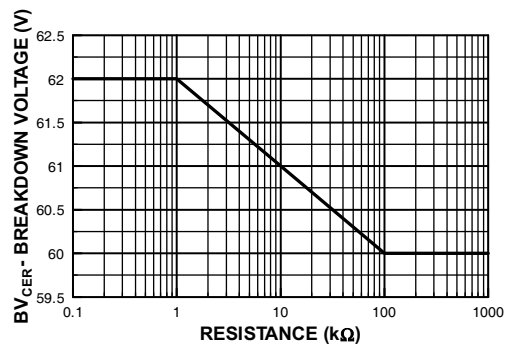


Figure 6. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

Typical Performance Characteristics (Continued)

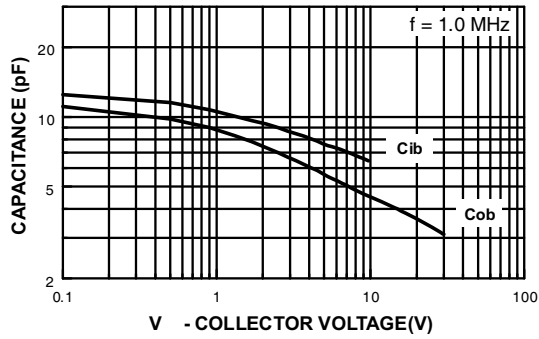


Figure 7. Input and Output Capacitance vs. Reverse Voltage

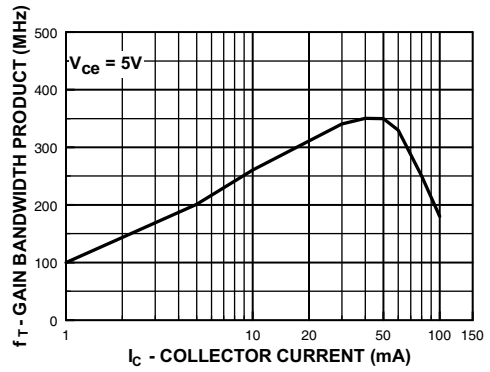


Figure 8. Gain Bandwidth Product vs. Collector Current

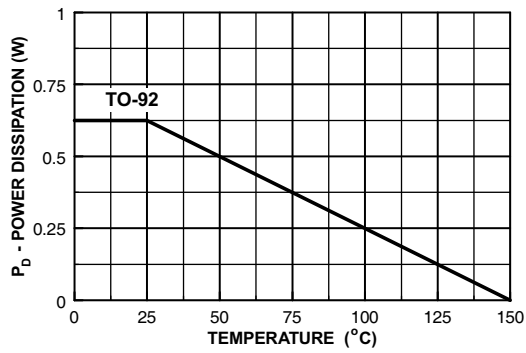
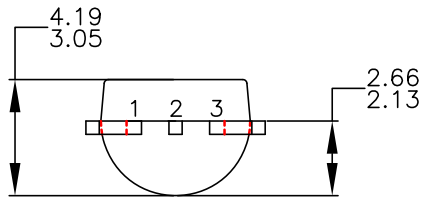
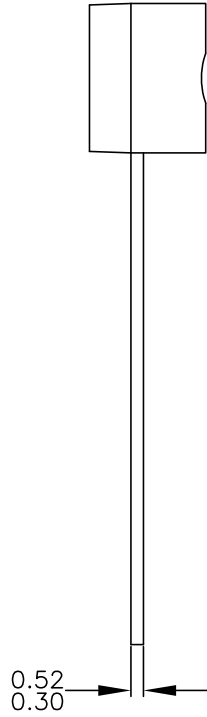
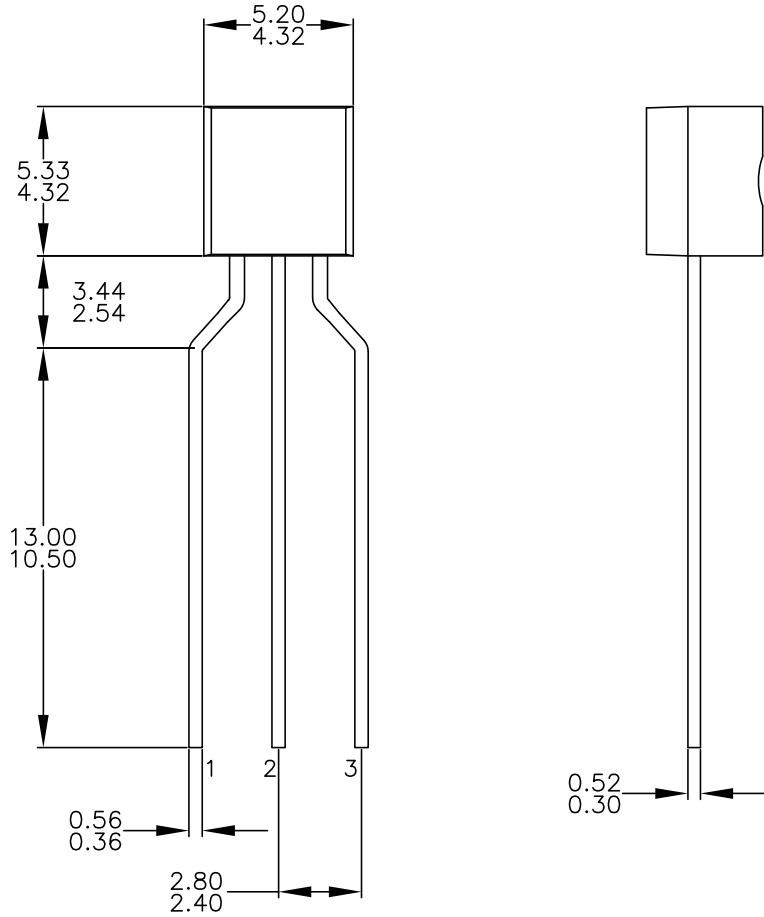


Figure 9. Power Dissipation vs. Ambient Temperature

Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. ON SEMICONDUCTOR

Figure 10. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Packing

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